

ABSTRACT OF THE DISCLOSURE

An SiC fabrication comprising a CVD-SiC fabrication excellent in strength and thermal characteristics. The SiC fabrication is prepared with a CVD process (i.e. CVD-SiC fabrication) which has a thermal conductivity along the direction of the SiC crystal growth between 100 and 300 W/m·K, and an average grain diameter of the internal structure between 4 to 12 μm . It is preferred that the ratio of the thermal conductivity along the direction of the SiC crystal growth to the thermal conductivity in the perpendicular direction is in a range of 1.10 to 1.40.

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